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# All-Optical Switching in 2-D Photonic Crystal Cavities with Defect Resonances.

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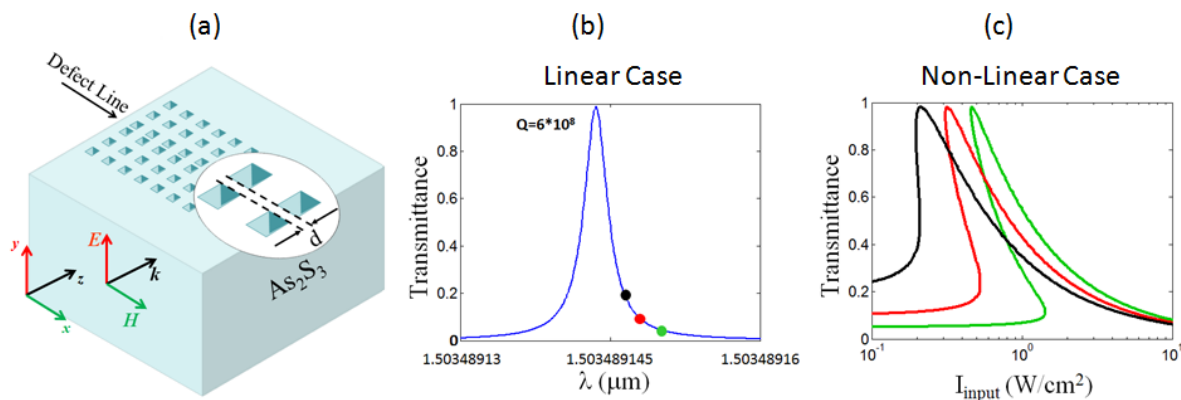
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**Abstract:** We investigate the field localization in 2-D photonic crystals with defect resonances for all-optical switching applications. These resonances achieve extremely high Q factors  $\sim 10^8$  and switching threshold  $\sim \text{W}/\text{cm}^2$  for realistic values of the cubic nonlinearity.

**OCIS codes** (160.5298) Photonic crystals ; (230.4320) Nonlinear optical devices.

The ability to confine light in extremely small volumes is crucial for enhancing many light-matter interaction phenomena such as surface enhanced Raman scattering [1], quantum-dot [2] and quantum-well emission [3]. In this work we investigate the field localization properties in a chalcogenide glass ( $\text{As}_2\text{S}_3$ ), 2-D photonic crystal (PC) cavity with a defect line, as in Fig.1(a). Although based on a simple geometry, the structure gives rise to defect resonances with extremely high quality (Q)-factors  $\sim 10^8$ , as shown in Fig.1(b). In Fig.1(c) it is presented an example of all-optical switching at telecommunication wavelengths obtained for input intensity  $\sim \text{W}/\text{cm}^2$  and local field intensity in the crystal well below the photodarkening threshold of the material.



**Figure 1:** (a) 2-D PC slab with a line defect of thickness  $d$  located at its center. The slab is made of  $\text{As}_2\text{S}_3$  for in-plane coupling of the incident radiation, i.e. the  $k$ -vector of the incident wave lies parallel to the  $(x,z)$  plane and forms an angle  $\theta$  with the  $z$  axis. The PC is made by drilling holes of square section  $a \times a$  arranged in a periodic array with periodicity  $\Lambda$  on both directions. The polarization of the electric field is along the  $y$ -axis, parallel to the axis of the holes. In our case  $a=450\text{nm}$ ,  $\Lambda=900\text{nm}$ . The PC slab is finite along the  $z$  direction and has total length  $L=N\Lambda$  with  $N=30$  periods, it starts at  $z=0$  and ends at  $z=L=27\mu\text{m}$ . We consider  $\text{As}_2\text{S}_3$  be the input medium ( $z<0$ ) as well as the output medium ( $z>L$ ). (b) Normal incidence linear transmittance vs. incident wavelength for the defect resonance that shows a quality factor  $Q \sim 6 \cdot 10^8$ . The black, red and green dots respectively indicate the tuning condition of the impinging wave used for the nonlinear calculation. (c) Nonlinear transmittance vs. input intensity for the tuning conditions described in (b).

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